# UTC UNISONIC TECHNOLOGIES CO., LTD

## BCV47

### **Preliminary**

#### NPN SILICON TRANSISTOR

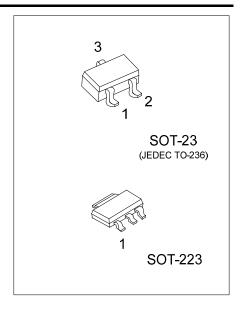
## NPN DARLINGTON TRANSISTOR

#### **DESCRIPTION**

The UTC BCV47 is a NPN Darlington transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

#### **FEATURES**

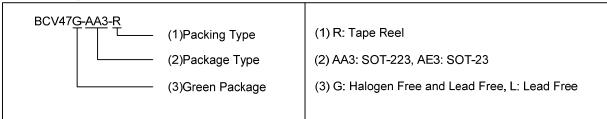
\* Medium current: max. 500mA



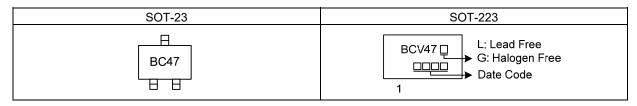
#### ORDERING INFORMATION

Ordering Number		Daakana	Pin Assignment			Dealine	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BCV47L-AA3-R	BCV47G-AA3-R	SOT-223	В	С	Е	Tape Reel	
BCV47L-AE3-R	BCV47G-AE3-R	SOT-23	В	E	С	Tape Reel	

Note: Pin Assignment: B: Base C: Case E: Emitter



#### **MARKING**



www.unisonic.com.tw 1 of 3

<sup>\*</sup> Low voltage: max. 60V

#### ■ ABSOLUATE MAXIUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V <sub>CBO</sub>	80	V	
Collector-Emitter Voltage		Vces	60	V	
Emitter-Base Voltage		V <sub>EBO</sub>	10	V	
Base Current		lΒ	100	mA	
Collector Current (DC)		lc	500	mA	
Peak Collector Current		Ісм	800	mA	
Collector Power Dissipation	SOT-223		600	mW	
(Note 2)	SOT-23	Pc	250	mW	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T <sub>STG</sub>	-65 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	SOT-223	0	208.3	°C/W	
	SOT-23	θја	500	°C/W	
Junction to Case	SOT-223	0	20	°C/W	
	SOT-23	θЈс	100	°C/W	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	ВУсво	Ic=100μA	80			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	Ic=10mA	60			V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =10μA	10			V
Collector Cut-off Current	Ісво	V <sub>CBO</sub> =60V, I <sub>E</sub> =0			100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =10V, I <sub>E</sub> =0			100	nA
		V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	2000			
DC Current Gain (Note)		V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	4000			
		V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	10000			
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =0.1mA			1	<b>V</b>
Base-Emitter Saturation Voltage (Note)	$V_{BE(SAT)}$	I <sub>C</sub> =100mA, I <sub>B</sub> =0.1mA			1.5	<b>V</b>
Base Emitter On Voltage (Note)	$V_{BE(ON)}$	Ic=10mA, VcE=5V			1.4	V

Note: Pulse test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.

<sup>2.</sup> Transistor mounted on an FR4 printed-circuit board.

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